

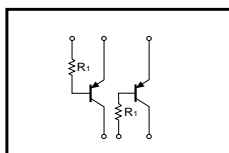
General purpose (dual digital transistors)

IMB7A

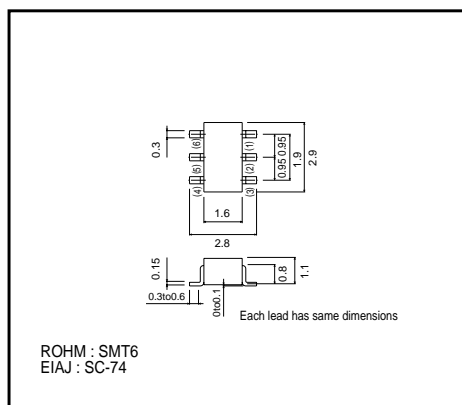
●Features

1) Two DTA143T chips in a SMT package.

●Circuit diagram



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-50	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-100	mA
Collector power dissipation	P _c	300(TOTAL)	mW *
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55→+150	°C

* 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Type	IMB7A
Package	SMT6
Marking	B7
Code	T110
Basic ordering unit (pieces)	3000

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-50	-	-	V	I _c =-50μA
Collector-emitter breakdown voltage	BV _{CE0}	-50	-	-	V	I _c =-1mA
Emitter-base breakdown voltage	BV _{EB0}	-5	-	-	V	I _E =-50μA
Collector cutoff current	I _{cbo}	-	-	-0.5	μA	V _{CB} =-50V
Emitter cutoff current	I _{EBO}	-	-	-0.5	μA	V _{EB} =-4V
DC current transfer ratio	h _{FE}	100	250	600	-	V _{CE} /I _C =-5V/-1mA
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	-0.3	V	I _C /I _B =-5mA/-0.25mA
Input resistance	R ₁	3.29	4.7	6.11	kΩ	-